

**Product data sheet** 

### 1. General description

Dual ultrafast power diode in TO263 (D2PAK) plastic package.

#### 2. Features and benefits

- Low on-state loss
- Ultra low leakage
- Fast switching
- Soft recovery characteristic minimizes power consuming oscillations
- High reverse surge capability
- High thermal cycling performance
- Low thermal resistance

### 3. Applications

Home appliance power supply

### 4. Quick reference data

Symbol	Parameter	Conditions		Values		Unit
Absolute	e maximum rating					
V <sub>RRM</sub>	repetitive peak reverse voltage			200		V
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 143 °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3	20		A	
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 151 °C; square-wave pulse ; per diode		20		A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	125			A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode		137		A
I <sub>RRM</sub>	repetitive peak reverse current	square-wave pulse; f = 1 kHz; $t_p$ = 2 µs; per diode	0.2		A	
$V_{\text{ESD}}$	electrostatic discharge voltage	all pin; human body model; C = 250 pF; R = 1.5 k $\Omega$	8		kV	
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V <sub>F</sub>	forward voltage	$I_F$ = 20A; $T_j$ = 25 °C; per diode; Fig. 6	-	1.06	1.15	V
		$I_{F} = 8 \text{ A}; T_{j} = 150 \text{ °C}; \text{ per diode}; Fig. 6$	-	0.76	0.85	V
Dynamic	characteristics					
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 7</u>	-	18	25	ns

# **5. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	А	anode	mb	
2	К	cathode		
3	А	anode		K sym125
mb	mb	mounting base; connected to cathod		

# 6. Ordering information

Table 3. Ordering inform	nation					
Type number	Package	Package				
	Name	Description	Version			
BYV32EB-200P	TO-263	plastic single-ended surface-mounted package (DPAK); 3-leads (one lead cropped)	DPAK			

## 7. Marking

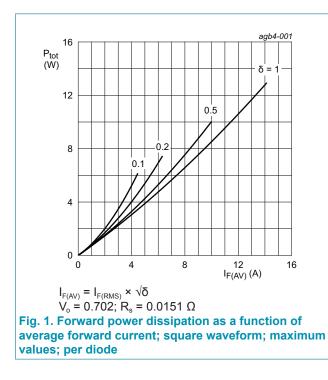
Table 4. Marking codes						
	Type number	Marking codes				
	BYV32EB-200P	BYV32EB-200P				

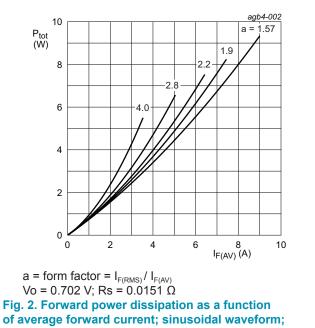
### 8. Limiting values

#### Table 5. Limiting values

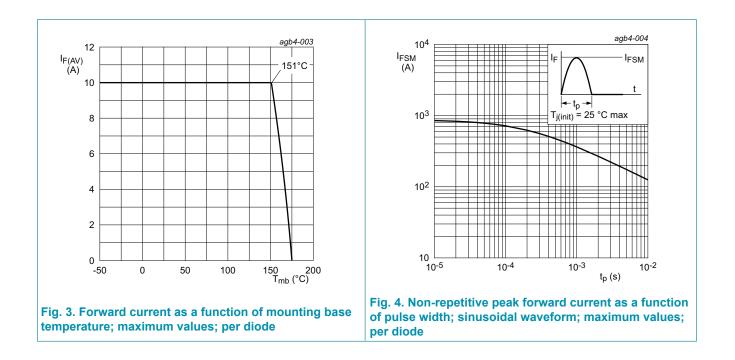
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		200	V
V <sub>RWM</sub>	crest working reverse voltage		200	V
V <sub>R</sub>	reverse voltage	DC	200	V
I <sub>O(AV)</sub>	average output current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 143 °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3	20	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 151 °C; square-wave pulse ; per diode	20	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	125	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	137	A
I <sub>RRM</sub>	repetitive peak reverse current	square-wave pulse; f = 1 kHz; $t_p$ = 2 µs; per diode	0.2	A
I <sub>RSM</sub>	non-repetitive peak reverse current	square-wave pulse; $t_p$ = 100 µs; per diode	0.2	A
T <sub>stg</sub>	storage temperature		-65 to 175	°C
Г <sub>ј</sub>	junction temperature		175	°C
V <sub>ESD</sub>	electrostatic discharge voltage	all pin; human body model; C = 250 pF; R = 1.5 k $\Omega$	8	8kV





maximum values; per diode

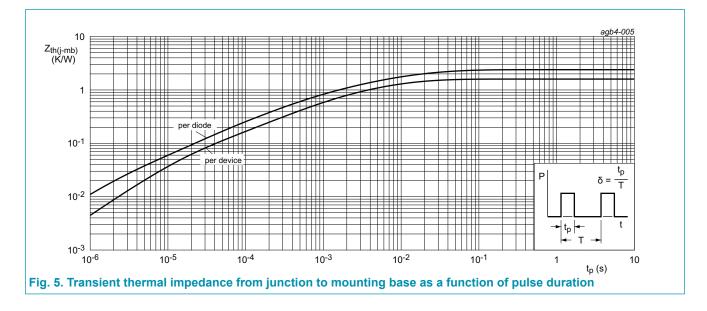


BYV32EB-200P

**Dual ultrafast power diodes** 

## 9. Thermal characteristics

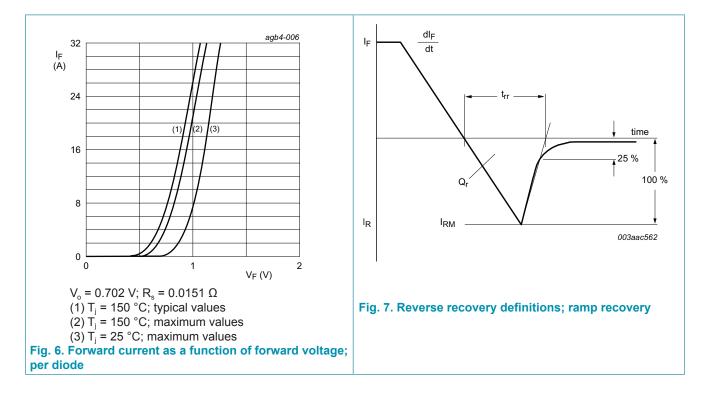
Table 6. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	per diode; <u>Fig. 5</u>	-	-	2.4	K/W
		both diodes conducting; Fig. 5	-	-	1.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	50	-	K/W



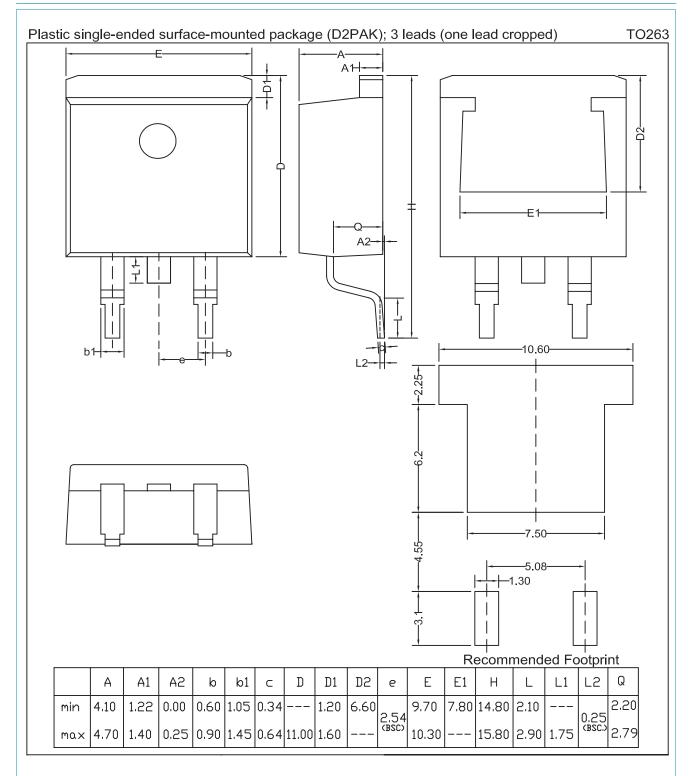
Dual ultrafast power diodes

### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics	· · · · ·				
V <sub>F</sub>	forward current	$I_{F} = 20 \text{ A}; T_{j} = 25 \text{ °C}; \text{ per diode}; Fig. 6$	-	1.06	1.15	V
		$I_F = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 6$	-	0.95	-	V
		$I_{F} = 8 \text{ A}; T_{j} = 150 \text{ °C}; \text{ per diode}; Fig. 6$	-	0.76	0.85	V
I <sub>R</sub>	reverse current	$V_R$ = 200 V; T <sub>j</sub> = 25 °C; per diode	-	0.3	5	μA
		V <sub>R</sub> = 200 V; T <sub>j</sub> = 150 °C; per diode	-	70	250	μA
Dynamic	characteristics	· /	I			,
Q <sub>r</sub>	reverse charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	14.5	-	nC
		$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$		13.5	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	18	25	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_i = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	1.7	-	A



## **11. Package outline**



### BYV32EB-200P

#### **Dual ultrafast power diodes**

## 12. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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